

DIODE Silicon Epitaxial Planar Type

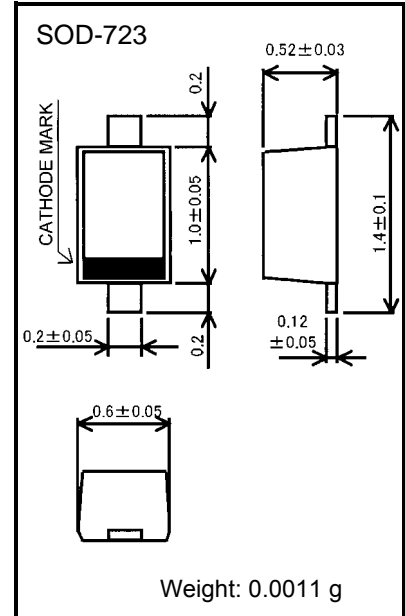
VCO for UHF Band Radio

Unit: mm

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	$V_R$	10	V
Junction temperature	$T_j$	150	°C
Storage temperature range	$T_{stg}$	-55~150	°C

- High Capacitance Ratio:  $C_{1V}/C_{4V} = 2.3$  (typ.)
- Low Series Resistance :  $r_s = 0.42 \Omega$  (typ.)
- This device is suitable for use in a small-size tuner.



Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	$V_R$	$I_R = 1 \mu A$	10	—	—	V
Reverse current	$I_R$	$V_R = 10 V$	—	—	3	nA
Capacitance	$C_{1V}$	$V_R = 1 V, f = 1 MHz$	4.0	4.5	4.9	pF
	$C_{4V}$	$V_R = 4 V, f = 1 MHz$	1.85	2.0	2.35	
Capacitance ratio	$C_{1V}/C_{4V}$	—	2.0	2.3	—	—
Series resistance	$r_s$	$V_R = 1 V, f = 470 MHz$	—	0.42	0.55	$\Omega$

Note: Signal level when capacitance is measured:  $V_{sig} = 500 mV_{rms}$



Marking

